

Supplementary Information

Indoor Light-Activated Cone-Shaped MoS₂ Gas Sensor for

Room-temperature ppb-level Detection on NO Gas

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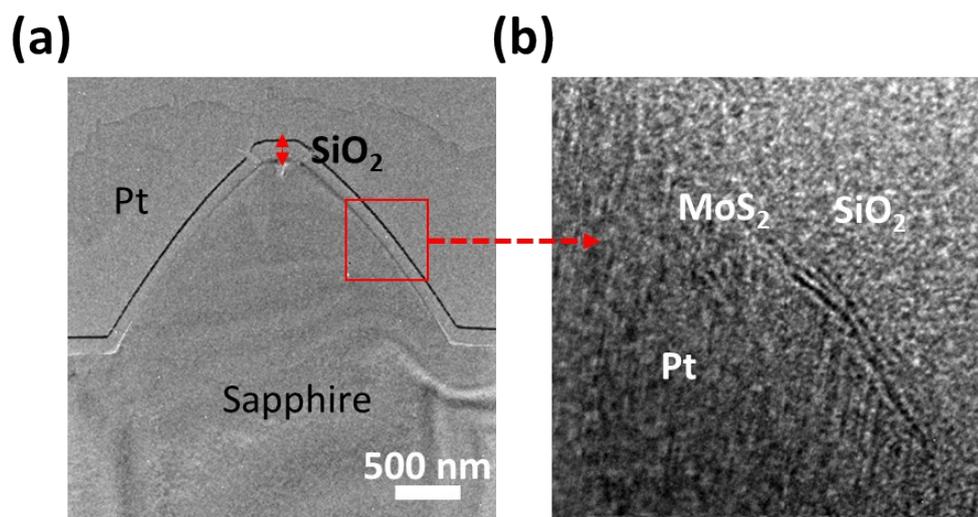


Figure S1 (a) TEM images of MoS₂ grown on cone-shaped sapphire substrate. (b) Enlarged view of (a), confirming the discontinuity of monolayer MoS₂.

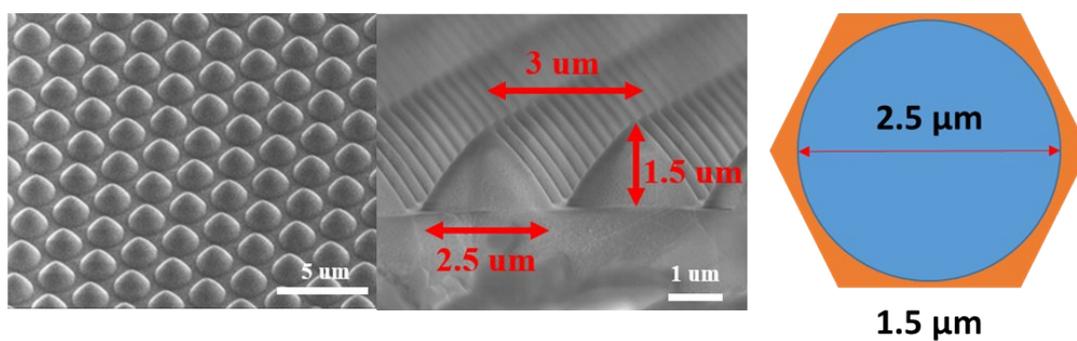


Figure S2 SEM images of cones periodically arranged on sapphire with their corresponding size. Flat area of $5.85 \mu\text{m}^2$ can be given by $6 \times 1.5 \times 1.3 \times 0.5$ while surface area of $7.64 \mu\text{m}^2$ per cone can be given by $1.95 \times 1.95 \times \pi \times 0.64$, yielding the ratio between flat area and surface area per cone being 1.3 by $\frac{7.64}{5.85}$.

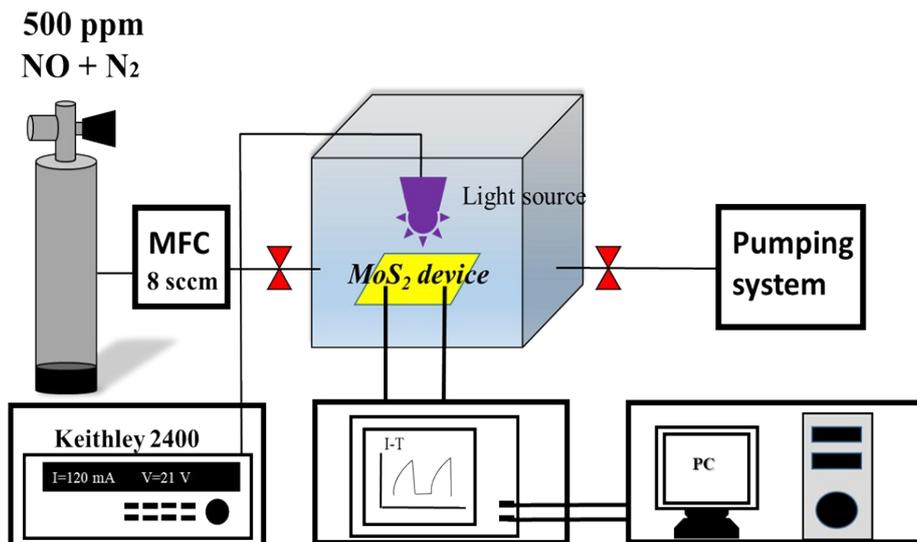


Figure S3 Schematic of the hand-made gas sensor measurements including a chamber and a stage where the light source was installed and linked to a Keithley system. Mass flow controller (MFC) controls the concentrations of NO and N₂ gases.

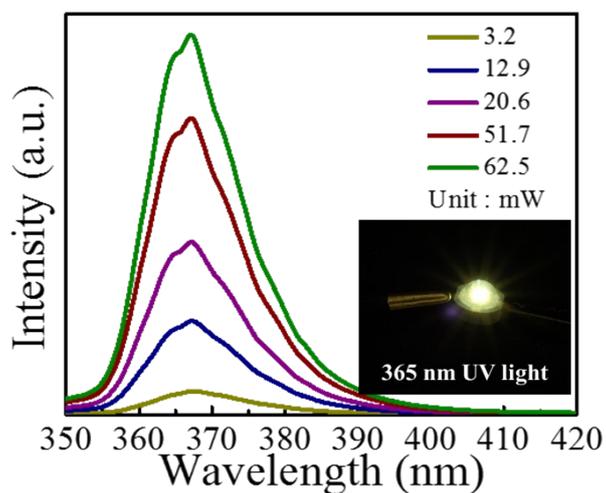


Figure S4 The radiant flux of UV light with the wavelength of 365 nm as the functions of emitting powers.

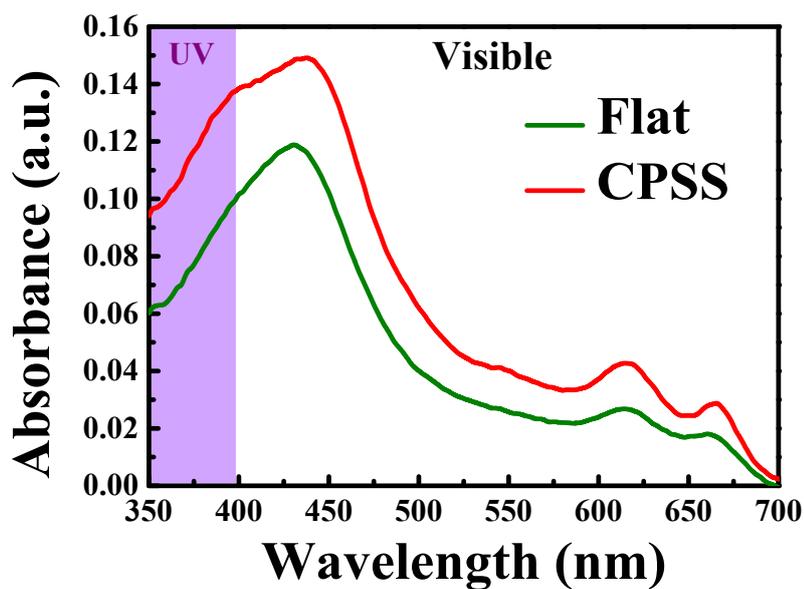


Figure S5 UV-Vis absorption spectra of F-MoS₂ (green) and CS-MoS₂ (red).

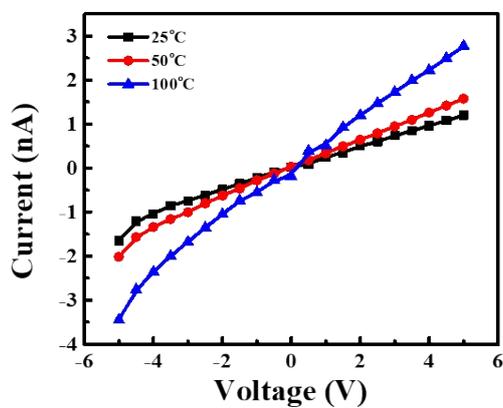


Figure S6 I-V characteristics of F-MoS₂ GS measured at 25 (black), 50 (red) and 100 °C (blue), respectively. The conductance of MoS₂ bilayers increases as temperature increases, confirming a semiconductor property of MoS₂ bilayers.

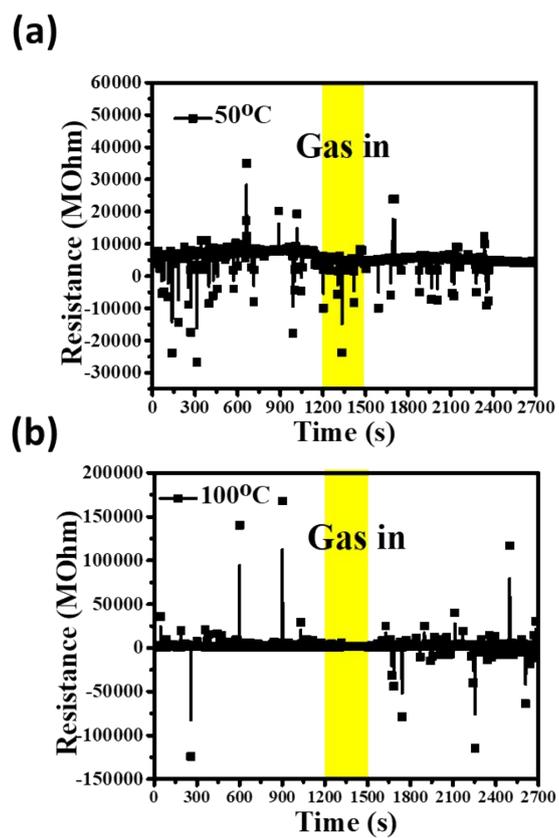


Figure S7 1ppm NO gas sensing measurements of F-MoS₂ GS at operating temperatures of (a) 50 °C, (b) 100 °C. The sluggish response was proved that our devices would not be promoted by heating.

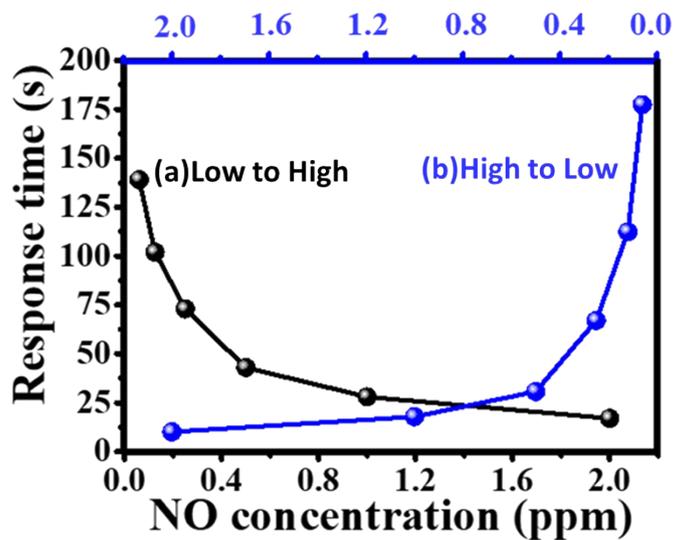


Figure S8 A plot of response time as a dependence of NO concentration gradient from (a) low to high and (b) high to low.

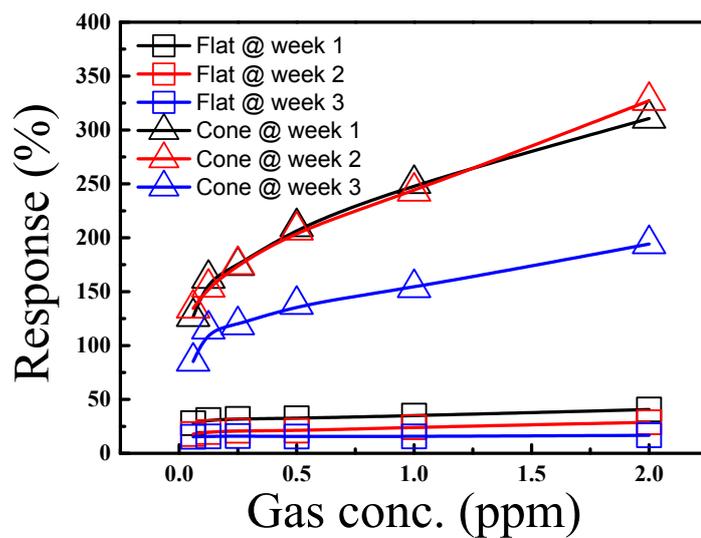


Figure S9 A plot of response over 3 weeks as a dependence of NO concentration gradient for both F-MoS₂ GS and CS-MoS₂ GS.

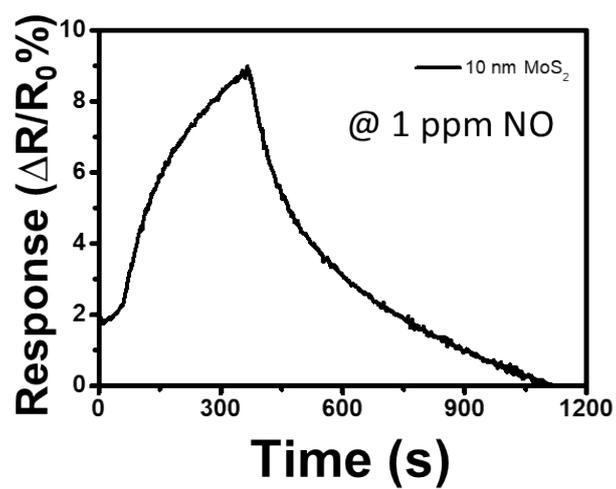


Figure S10 1ppm NO gas sensing measurements of C-MoS₂ GS with layered thickness of 10 nm at operating temperatures

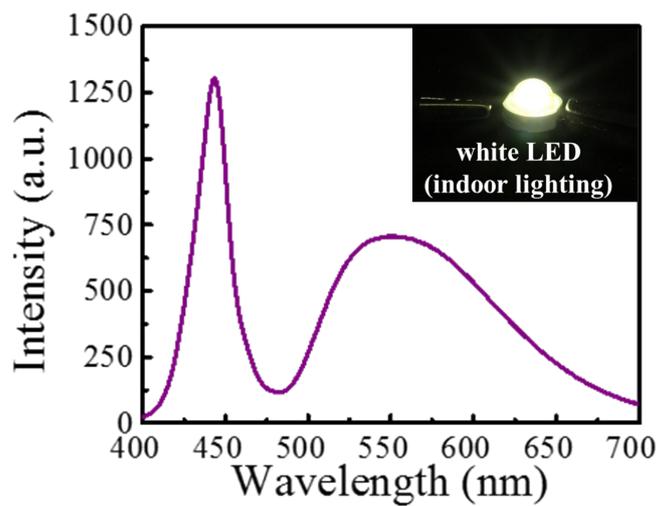


Figure S11 The radiant flux of the white-light LED. Inset shows an image of a white-light LED for the indoor lighting.